

## High Speed CMOS Logic 4-Bit Magnitude Comparator

### **Features**

- Buffered Inputs and Outputs
- Typical Propagation Delay: 13ns (Data to Output at  $V_{CC} = 5V$ ,  $C_L = 15pF$ ,  $T_A = 25^\circ C$ )
- Serial or Parallel Expansion Without External Gating
- Fanout (Over Temperature Range)
  - Standard Outputs ..... 10 LSTTL Loads
  - Bus Driver Outputs ..... 15 LSTTL Loads
- Wide Operating Temperature Range ...  $-55^\circ C$  to  $125^\circ C$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity:  $N_{IL} = 30\%$ ,  $N_{IH} = 30\%$  of  $V_{CC}$  at  $V_{CC} = 5V$
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility,  $V_{IL} = 0.8V$  (Max),  $V_{IH} = 2V$  (Min)
  - CMOS Input Compatibility,  $I_I \leq 1\mu A$  at  $V_{OL}$ ,  $V_{OH}$

### **Description**

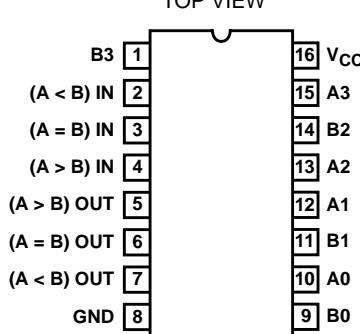
The 'HC85 and 'HCT85 are high speed magnitude comparators that use silicon-gate CMOS technology to achieve operating speeds similar to LSTTL with the low power consumption of standard CMOS integrated circuits.

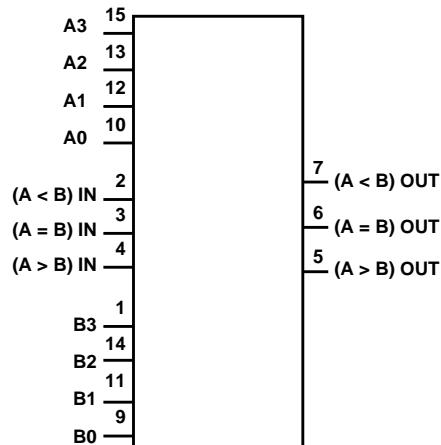
### **Pinout**

**CD54HC85, CD54HCT85  
(CERDIP)**

**CD74HC85, CD74HCT85  
(PDIP, SOIC)**

**TOP VIEW**



***Functional Diagram*****TRUTH TABLE**

COMPARING INPUTS				CASCADING INPUTS			OUTPUTS		
A3, B3	A2, B2	A1, B1	A0, B0	A > B	A < B	A = B	A > B	A < B	A = B
<b>SINGLE DEVICE OR SERIES CASCADING</b>									
A3 > B3	X	X	X	X	X	X	H	L	L
A3 < B3	X	X	X	X	X	X	L	H	L
A3 = B3	A2 > B2	X	X	X	X	X	H	L	L
A3 = B3	A2 < B2	X	X	X	X	X	L	H	L
A3 = B3	A2 = B2	A1 > B1	X	X	X	X	H	L	L
A3 = B3	A2 = B2	A1 < B1	X	X	X	X	L	H	L
A3 = B3	A2 = B2	A1 = B1	A0 > B0	X	X	X	H	L	L
A3 = B3	A2 = B2	A1 = B1	A0 < B0	X	X	X	L	H	L
A3 = B3	A2 = B2	A1 = B1	A0 = B0	H	L	L	H	L	L
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	H	L	L	H	L
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	L	H	L	L	H
<b>PARALLEL CASCADING</b>									
A3 = B3	A2 = B2	A1 = B1	A0 = B0	X	X	H	L	L	H
A3 = B3	A2 = B2	A1 = B1	A0 = B0	H	H	L	L	L	L
A3 = B3	A2 = B2S	A1 = B1	A0 = B0	L	L	L	H	H	L

NOTE: H = High Voltage Level, L = Low Voltage Level, X = Don't Care

**Absolute Maximum Ratings**

DC Supply Voltage, V <sub>CC</sub> .....	-0.5V to 7V
DC Input Diode Current, I <sub>IK</sub>	
For V <sub>I</sub> < -0.5V or V <sub>I</sub> > V <sub>CC</sub> + 0.5V .....	±20mA
DC Output Diode Current, I <sub>OK</sub>	
For V <sub>O</sub> < -0.5V or V <sub>O</sub> > V <sub>CC</sub> + 0.5V .....	±20mA
DC Output Source or Sink Current per Output Pin, I <sub>O</sub>	
For V <sub>O</sub> > -0.5V or V <sub>O</sub> < V <sub>CC</sub> + 0.5V .....	±25mA
DC V <sub>CC</sub> or Ground Current, I <sub>CC</sub> or I <sub>GND</sub> .....	±50mA

**Thermal Information**

Thermal Resistance (Typical, Note 3)	θ <sub>JA</sub> (°C/W)
PDIP Package .....	90
SOIC Package .....	190
Maximum Junction Temperature .....	150°C
Maximum Storage Temperature Range .....	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s) .....	300°C
(SOIC - Lead Tips Only)	

**Operating Conditions**

Temperature Range (T <sub>A</sub> ) .....	-55°C to 125°C
Supply Voltage Range, V <sub>CC</sub>	
HC Types .....	.2V to 6V
HCT Types .....	.4.5V to 5.5V
DC Input or Output Voltage, V <sub>I</sub> , V <sub>O</sub> .....	0V to V <sub>CC</sub>
Input Rise and Fall Time	
2V .....	1000ns (Max)
4.5V .....	500ns (Max)
6V .....	400ns (Max)

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

## NOTE:

3. θ<sub>JA</sub> is measured with the component mounted on an evaluation PC board in free air.

**DC Electrical Specifications**

PARAMETER	SYMBOL	TEST CONDITIONS		V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS		
		V <sub>I</sub> (V)	I <sub>O</sub> (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX			
<b>HC TYPES</b>														
High Level Input Voltage	V <sub>IH</sub>	-	-	2	1.5	-	-	1.5	-	1.5	-	V		
				4.5	3.15	-	-	3.15	-	3.15	-	V		
				6	4.2	-	-	4.2	-	4.2	-	V		
Low Level Input Voltage	V <sub>IL</sub>	-	-	2	-	-	0.5	-	0.5	-	0.5	V		
				4.5	-	-	1.35	-	1.35	-	1.35	V		
				6	-	-	1.8	-	1.8	-	1.8	V		
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	2	1.9	-	-	1.9	-	1.9	-	V		
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V		
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V		
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V		
			-4	4.5	3.98	-	-	3.84	-	3.7	-	V		
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V		
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	2	-	-	0.1	-	0.1	-	0.1	V		
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V		
			0.02	6	-	-	0.1	-	0.1	-	0.1	V		
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V		
			5.2	6	-	-	0.26	-	0.33	-	0.4	V		
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> or GND	-	6	-	-	±0.1	-	±1	-	±1	µA		
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	6	-	-	8	-	80	-	160	µA		

# CD54/74HC85, CD54/74HCT85

## DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V <sub>I</sub> (V)	I <sub>O</sub> (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HCT TYPES</b>												
High Level Input Voltage	V <sub>IH</sub>	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> and GND	0	5.5	-		±0.1	-	±1	-	±1	µA
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	5.5	-	-	8	-	80	-	160	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note)	ΔI <sub>CC</sub>	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE: For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

## HCT Input Loading Table

INPUT	UNIT LOADS
A0-A3, B0-B3 and (A = B) IN	1.5
(A > B) IN, (A < B) IN	1

NOTE: Unit Load is ΔI<sub>CC</sub> limit specified in DC Electrical Table, e.g. 360µA max at 25°C.

## Switching Specifications Input t<sub>r</sub>, t<sub>f</sub> = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>											
Propagation Delay, A <sub>n</sub> , B <sub>n</sub> to (A > B) OUT, (A < B) OUT	t <sub>PLH</sub> , t <sub>PHL</sub>	C <sub>L</sub> = 50pF	2	-	-	195	-	245	-	295	ns
		4.5	-	-	-	39	-	47	-	59	ns
		C <sub>L</sub> = 15pF	5	-	16	-	-	-	-	-	ns
		C <sub>L</sub> = 50pF	6	-	-	33	-	42	-	50	ns
A <sub>n</sub> , B <sub>n</sub> to (A = B) OUT	t <sub>PLH</sub> , t <sub>PHL</sub>	C <sub>L</sub> = 50pF	2	-	-	175	-	240	-	265	ns
		4.5	-	-	35	-	44	-	53	ns	
		C <sub>L</sub> = 15pF	5	-	14	-	-	-	-	-	ns
		C <sub>L</sub> = 50pF	6	-	-	30	-	37	-	45	ns

**Switching Specifications** Input  $t_r, t_f = 6\text{ns}$  (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	$V_{CC}$ (V)	25°C			-40°C TO 85°C		-55°C TO 125°C	
				MIN	TYP	MAX	MIN	MAX	MIN	MAX
(A > B) IN, (A < B) IN, (A = B) IN to (A > B) OUT, (A < B) OUT	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	2	-	-	140	-	175	-	210
			4.5	-	-	28	-	35	-	42
		$C_L = 15\text{pF}$	5	-	11	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	24	-	30	-	36
(A > B) IN to (A = B) OUT	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	2	-	-	120	-	150	-	180
			4.5	-	-	24	-	30	-	36
		$C_L = 15\text{pF}$	5	-	9	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	20	-	26	-	31
Power Dissipation Capacitance (Notes 4, 5)	$C_{PD}$	-	5	-	24	-	-	-	-	pF
Output Transition Times (Figure 1)	$t_{TLH}, t_{THL}$	$C_L = 50\text{pF}$	2	-	-	75	-	95	-	110
			4.5	-	-	15	-	19	-	22
			6	-	-	13	-	16	-	19
Input Capacitance	$C_{IN}$	-	-	-	-	10	-	10	-	10
<b>HCT TYPES</b>										
Propagation Delay, An, Bn to (A > B) OUT, (A < B) OUT	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	4.5	-	-	37	-	46	-	56
		$C_L = 15\text{pF}$	5	-	15	-	-	-	-	ns
An, Bn to (A = B) OUT	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	4.5	-	-	40	-	50	-	60
		$C_L = 15\text{pF}$	5	-	17	-	-	-	-	ns
(A > B) IN, (A < B) IN, (A = B) IN to (A > B) OUT, (A < B) OUT	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	4.5	-	-	30	-	38	-	45
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	ns
(A > B) IN to (A = B) OUT	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	4.5	-	-	31	-	39	-	47
		$C_L = 15\text{pF}$	5	-	13	-	-	-	-	ns
Output Transition Times (Figure 1)	$t_{TLH}, t_{THL}$	$C_L = 50\text{pF}$	4.5	-	-	15	-	19	-	22
Power Dissipation Capacitance (Notes 4, 5)	$C_{PD}$	-	5	-	26	-	-	-	-	pF
Input Capacitance	$C_{IN}$	-	-	-	-	10	-	10	-	10

## NOTES:

4.  $C_{PD}$  is used to determine the dynamic power consumption, per gate/package.
5.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

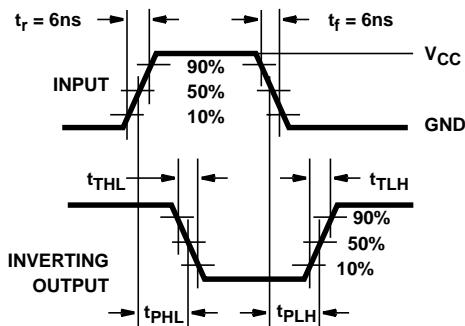
**Test Circuits and Waveforms**

FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

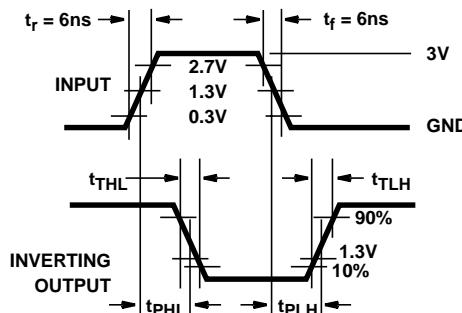


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

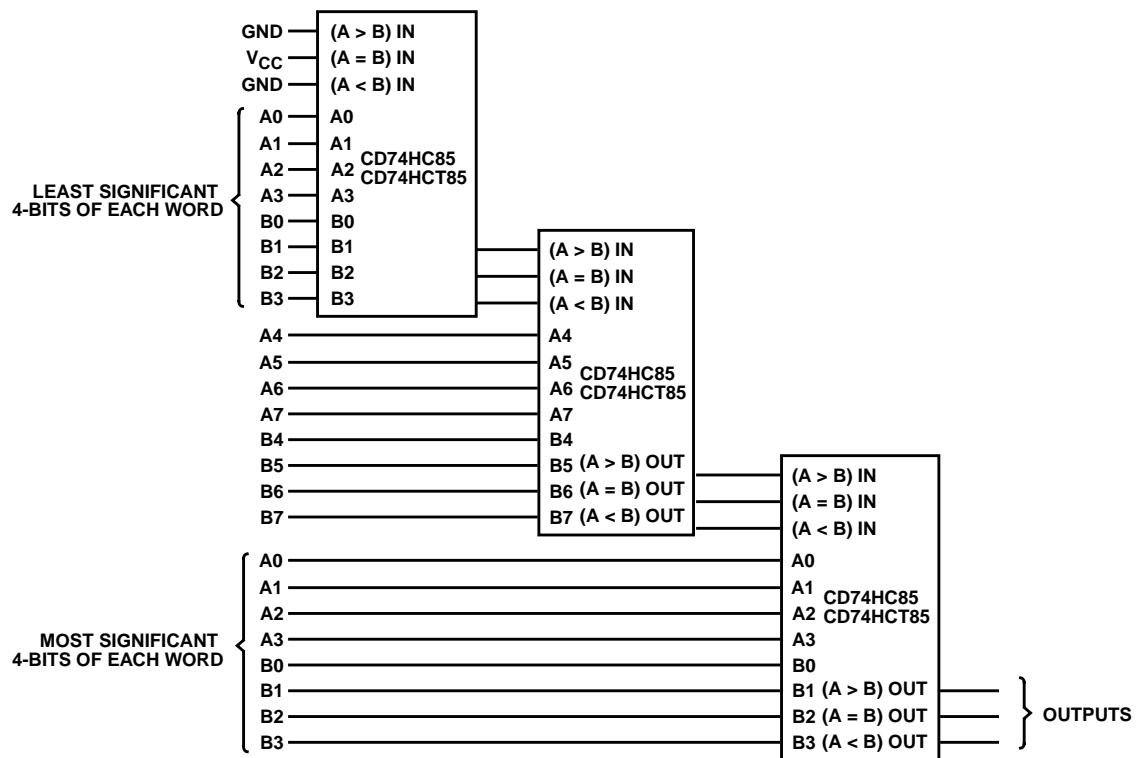
***Test Circuits and Waveforms***

FIGURE 3. SERIES CASCADING - COMPARING 12-BIT WORDS

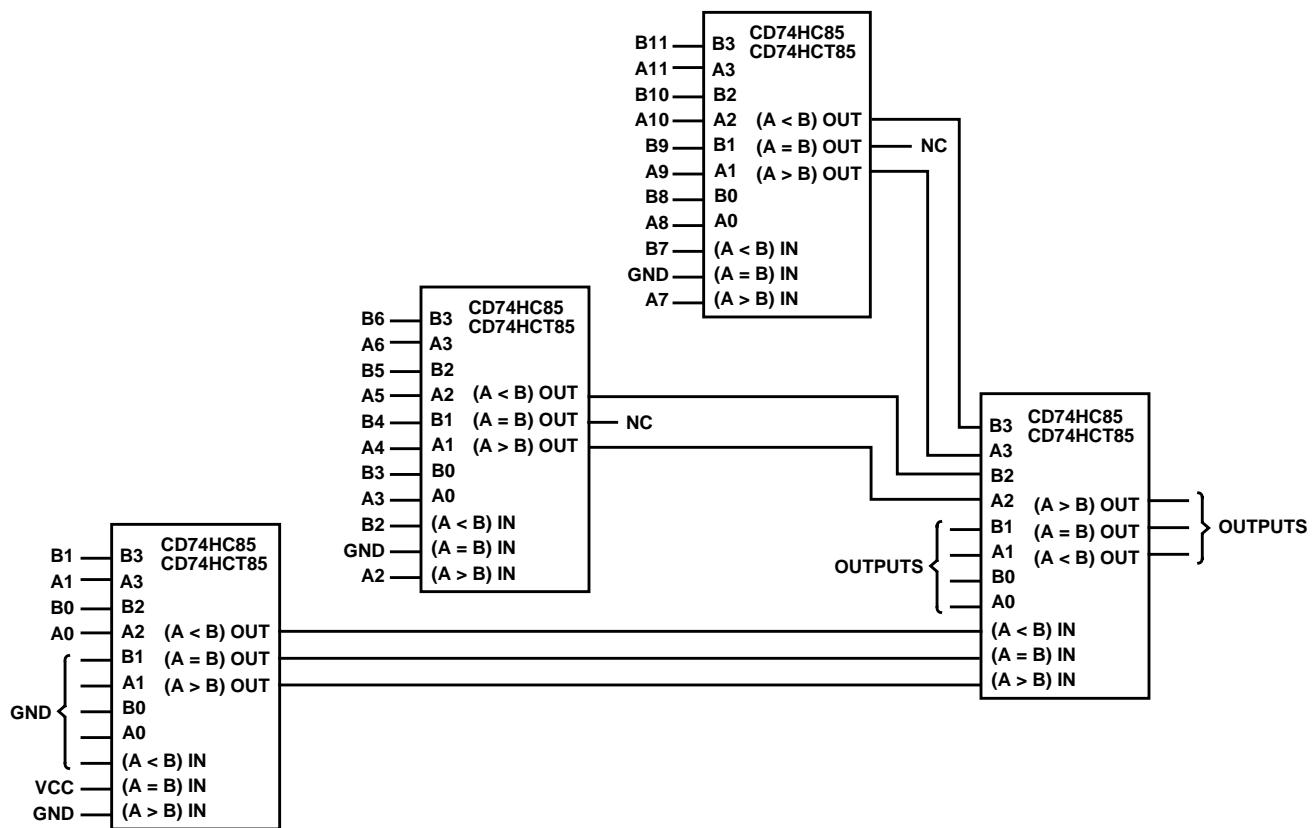
***Test Circuits and Waveforms***

FIGURE 4. PARALLEL CASCADING - COMPARING 12-BIT WORDS

### **IMPORTANT NOTICE**

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgment, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Customers are responsible for their applications using TI components.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 2000, Texas Instruments Incorporated